

Phuong Vuong

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. ACS Applied Materials & Interfaces, 2020, 12, 55460-55466.	4.0	14
2	Towards P-Type Conduction in Hexagonal Boron Nitride: Doping Study and Electrical Measurements Analysis of hBN/AlGaN Heterojunctions. Nanomaterials, 2021, 11, 211.	1.9	14
3	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. Scientific Reports, 2020, 10, 21709.	1.6	12
4	Single crystalline boron rich B(Al)N alloys grown by MOVPE. Applied Physics Letters, 2020, 116, .	1.5	12
5	Influence of Sapphire Substrate Orientation on the van der Waals Epitaxy of III-Nitrides on 2D Hexagonal Boron Nitride: Implication for Optoelectronic Devices. ACS Applied Nano Materials, 2022, 5, 791-800.	2.4	12
6	Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications. Advanced Materials Technologies, 2019, 4, 1900164.	3.0	10
7	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride—A key enabler of III-nitride flexible optoelectronics. APL Materials, 2021, 9, .	2.2	9
8	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. ACS Applied Electronic Materials, 2021, 3, 2614-2621.	2.0	8
9	Natural Boron and ¹⁰ B-Enriched Hexagonal Boron Nitride for High-Sensitivity Self-Biased Metal-Semiconductor-Metal Neutron Detectors. ACS Omega, 2022, 7, 804-809.	1.6	6